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August 2011

## FDD24AN06LA0\_F085

# N-Channel Logic Level PowerTrench® MOSFET 60V, 36A, 24m $\Omega$

#### **Features**

- $r_{DS(ON)} = 20m\Omega$  (Typ.),  $V_{GS} = 5V$ ,  $I_{D} = 36A$
- $Q_g(tot) = 16nC (Typ.), V_{GS} = 5V$
- · Low Miller Charge
- · Low Q<sub>RR</sub> Body Diode
- UIS Capability (Single Pulse and Repetitive Pulse)
- · Qualified to AEC Q101
- · RoHS Compliant

Formerly developmental type 83547



#### **Applications**

- · Motor / Body Load Control
- · ABS Systems
- · Powertrain Management
- · Injection Systems
- · DC-DC converters and Off-line UPS
- · Distributed Power Architectures and VRMs
- Primary Switch for 12V and 24V systems

#### DRAIN (FLANGE)



TO-252AA FDD SERIES



### **MOSFET Maximum Ratings** T<sub>C</sub> = 25°C unless otherwise noted

Symbol	Parameter	Ratings	Units
V <sub>DSS</sub>	Drain to Source Voltage	60	V
V <sub>GS</sub>	Gate to Source Voltage	±20	V
	Drain Current		
	Continuous ( $T_C = 25^{\circ}C$ , $V_{GS} = 10V$ )	40	Α
	Continuous ( $T_C = 25^{\circ}C$ , $V_{GS} = 5V$ )	36	А
ID	Continuous ( $T_C = 100^{\circ}C$ , $V_{GS} = 5V$ )	25	Α
	Continuous ( $T_A = 25^{\circ}C$ , $V_{GS} = 5V$ , $R_{\theta JA} = 52^{\circ}C/W$ )	7.1	Α
	Pulsed	Figure 4	Α
E <sub>AS</sub>	Single Pulse Avalanche Energy (Note 1)	32	mJ
P <sub>D</sub>	Power dissipation	75	W
	Derate above 25°C	0.5	W/°C
T <sub>J</sub> , T <sub>STG</sub>	Operating and Storage Temperature	-55 to 175	°C

#### **Thermal Characteristics**

$R_{\theta JC}$	Thermal Resistance Junction to Case TO-252	2.0	°C/W
$R_{\theta JA}$	Thermal Resistance Junction to Ambient TO-252	100	°C/W
$R_{\theta JA}$	Thermal Resistance Junction to Ambient TO-252, 1in <sup>2</sup> copper pad area	52	°C/W

This product has been designed to meet the extreme test conditions and environment demanded by the automotive industry. For a copy of the requirements, see AEC Q101 at: http://www.aecouncil.com/

Reliability data can be found at: http://www.fairchildsemi.com/products/discrete/reliability/index.html.

All Fairchild Semiconductor products are manufactured, assembled and tested under ISO9000 and QS9000 quality systems certification.

### **Package Marking and Ordering Information**

<b>Device Marking</b>	Device	Package	Reel Size	Tape Width	Quantity
FDD24AN06LA0	FDD24AN06LA0	TO-252AA	330mm	16mm	2500 units

# **Electrical Characteristics** $T_C = 25^{\circ}C$ unless otherwise noted

Symbol	Parameter	Test C	onditions	Min	Тур	Max	Units
Off Chara	acteristics						
B <sub>VDSS</sub>	Drain to Source Breakdown Voltage	$I_D = 250 \mu A, V_C$	<sub>SS</sub> = 0V	60	-	-	V
1	Zero Gate Voltage Drain Current	$V_{DS} = 50V$		-	-	1	μА
IDSS	Zero Gate Voltage Drain Guirent	$V_{GS} = 0V$	$T_{\rm C} = 150^{\rm o}{\rm C}$	-	-	250	μΑ
I <sub>GSS</sub>	Gate to Source Leakage Current	V <sub>GS</sub> = ±20V		-	-	±100	nA

#### **On Characteristics**

V <sub>GS(TH)</sub>	Gate to Source Threshold Voltage	$V_{GS} = V_{DS}$ , $I_D = 250\mu A$	1	-	2	V
r <sub>DS(ON)</sub> Drain to Source On Resistance		$I_D = 40A, V_{GS} = 10V$	-	0.016	0.019	
		$I_D = 36A, V_{GS} = 5V$	-	0.020	0.024	0
	$I_D = 36A, V_{GS} = 5V,$ $T_J = 175$ °C	-	0.047	0.056	32	

#### **Dynamic Characteristics**

C <sub>ISS</sub>	Input Capacitance	V <sub>DS</sub> = 25V, V <sub>GS</sub> = 0V, f = 1MHz		-	1850	-	pF
C <sub>OSS</sub>	Output Capacitance			-	180	-	pF
C <sub>RSS</sub>	Reverse Transfer Capacitance			-	75	-	pF
$Q_{g(TOT)}$	Total Gate Charge at 5V	$V_{GS} = 0V \text{ to } 5V$			16	21	nC
$Q_{g(TH)}$	Threshold Gate Charge	$V_{GS} = 0V \text{ to } 1V$	$V_{DD} = 30V$	-	1.8	2.4	nC
	Gate to Source Gate Charge		I <sub>D</sub> = 36A	-	6.3	-	nC
Q <sub>gs</sub> Q <sub>gs2</sub>	Gate Charge Threshold to Plateau		$I_g = 1.0 \text{mA}$	-	4.5	-	nC
$Q_{gd}$	Gate to Drain "Miller" Charge			-	5.0	-	nC

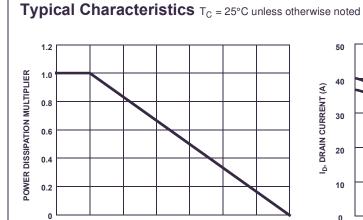
#### Switching Characteristics $(V_{GS} = 5V)$

t <sub>ON</sub>	Turn-On Time		-	-	195	ns
$t_{d(ON)}$	Turn-On Delay Time		-	12	-	ns
t <sub>r</sub>	Rise Time	$V_{DD} = 30V, I_{D} = 36A$	-	118	-	ns
t <sub>d(OFF)</sub>	Turn-Off Delay Time	$V_{GS} = 5V$ , $R_{GS} = 9.1\Omega$	-	26	-	ns
t <sub>f</sub>	Fall Time		-	41	-	ns
t <sub>OFF</sub>	Turn-Off Time		-	-	101	ns

#### **Drain-Source Diode Characteristics**

V <sub>SD</sub>	Source to Drain Diode Voltage	I <sub>SD</sub> = 36A	-	-	1.25	V
	Source to Drain blode voltage	I <sub>SD</sub> = 18A	-	-	1.0	V
t <sub>rr</sub>	Reverse Recovery Time	$I_{SD} = 36A$ , $dI_{SD}/dt = 100A/\mu s$	-	-	34	ns
Q <sub>RR</sub>	Reverse Recovered Charge	$I_{SD} = 36A$ , $dI_{SD}/dt = 100A/\mu s$	-	-	30	nC

**Notes:** 1: Starting  $T_J = 25^{\circ}C$ ,  $L = 80\mu H$ ,  $I_{AS} = 28A$ .



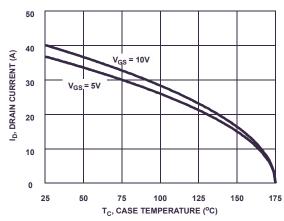


Figure 1. Normalized Power Dissipation vs Ambient Temperature

T<sub>C</sub>, CASE TEMPERATURE (°C)

75

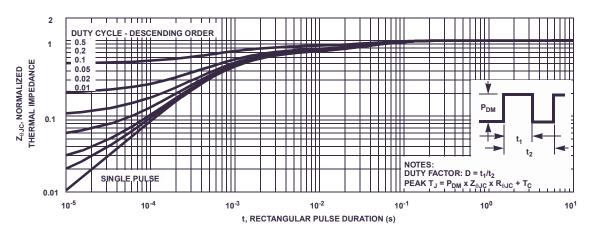
100

25

0

50

Figure 2. Maximum Continuous Drain Current vs
Case Temperature



150

125

175

Figure 3. Normalized Maximum Transient Thermal Impedance

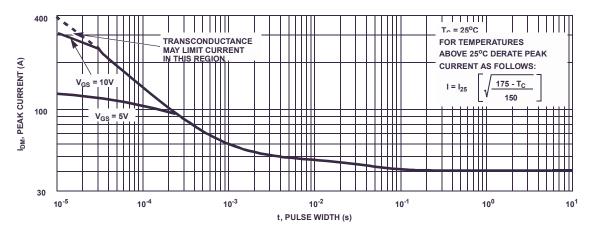


Figure 4. Peak Current Capability

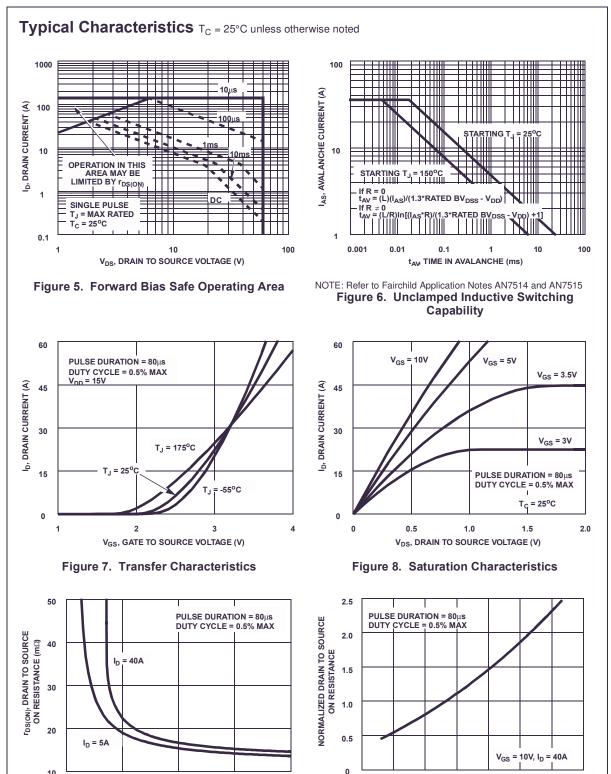


Figure 9. Drain to Source On Resistance vs Gate Voltage and Drain Current

V<sub>GS</sub>, GATE TO SOURCE VOLTAGE (V)

Figure 10. Normalized Drain to Source On Resistance vs Junction Temperature

40

T<sub>J</sub>, JUNCTION TEMPERATURE (°C)

80

120

160

-80

10

-40

10

2

200

# Typical Characteristics $T_C = 25^{\circ}C$ unless otherwise noted

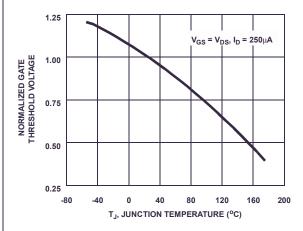


Figure 11. Normalized Gate Threshold Voltage vs Junction Temperature

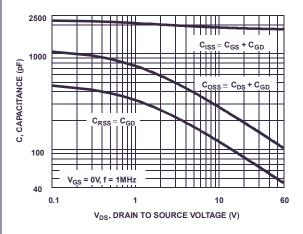


Figure 13. Capacitance vs Drain to Source Voltage

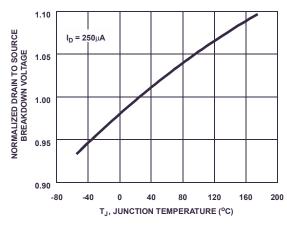


Figure 12. Normalized Drain to Source Breakdown Voltage vs Junction Temperature

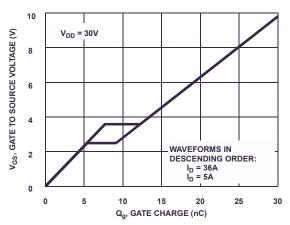


Figure 14. Gate Charge Waveforms for Constant Gate Current

#### **Test Circuits and Waveforms**

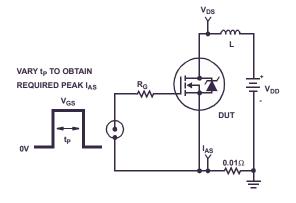


Figure 15. Unclamped Energy Test Circuit

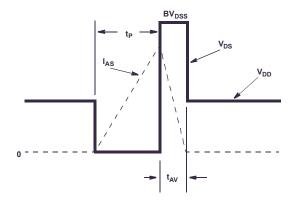


Figure 16. Unclamped Energy Waveforms

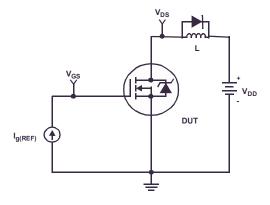


Figure 17. Gate Charge Test Circuit

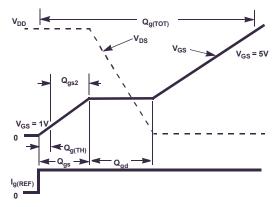


Figure 18. Gate Charge Waveforms

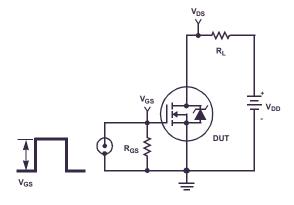


Figure 19. Switching Time Test Circuit

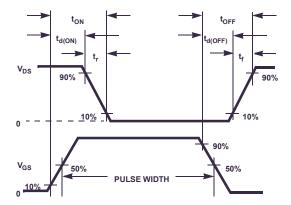


Figure 20. Switching Time Waveforms

#### Thermal Resistance vs. Mounting Pad Area

The maximum rated junction temperature,  $T_{JM}$ , and the thermal resistance of the heat dissipating path determines the maximum allowable device power dissipation,  $P_{DM}$ , in an application. Therefore the application's ambient temperature,  $T_A$  (°C), and thermal resistance  $R_{\theta JA}$  (°C/W) must be reviewed to ensure that  $T_{JM}$  is never exceeded. Equation 1 mathematically represents the relationship and serves as the basis for establishing the rating of the part.

$$P_{DM} = \frac{(T_{JM} - T_A)}{R_{\theta JA}} \tag{EQ. 1}$$

In using surface mount devices such as the TO-252 package, the environment in which it is applied will have a significant influence on the part's current and maximum power dissipation ratings. Precise determination of  $P_{DM}$  is complex and influenced by many factors:

- Mounting pad area onto which the device is attached and whether there is copper on one side or both sides of the board.
- The number of copper layers and the thickness of the board.
- 3. The use of external heat sinks.
- 4. The use of thermal vias.
- 5. Air flow and board orientation.
- For non steady state applications, the pulse width, the duty cycle and the transient thermal response of the part, the board and the environment they are in.

Fairchild provides thermal information to assist the designer's preliminary application evaluation. Figure 21 defines the  $R_{\theta JA}$  for the device as a function of the top copper (component side) area. This is for a horizontally positioned FR-4 board with 1oz copper after 1000 seconds of steady state power with no air flow. This graph provides the necessary information for calculation of the steady state junction temperature or power dissipation. Pulse applications can be evaluated using the Fairchild device Spice thermal model or manually utilizing the normalized maximum transient thermal impedance curve.

Thermal resistances corresponding to other copper areas can be obtained from Figure 21 or by calculation using Equation 2 or 3. Equation 2 is used for copper area defined in inches square and equation 3 is for area in centimeters square. The area, in square inches or square centimeters is the top copper area including the gate and source pads.

$$R_{\theta JA} = 33.32 + \frac{23.84}{(0.268 + Area)}$$
 (EQ. 2)

Area in Inches Squared

$$R_{\theta JA} = 33.32 + \frac{154}{(1.73 + Area)}$$
 (EQ. 3)

Area in Centimeters Squared

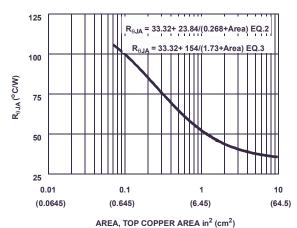


Figure 21. Thermal Resistance vs Mounting Pad Area





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